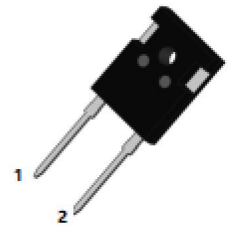
Technical Data
Data Sheet N2525, REV.-

S5D25170H
1700V SIC POWER SCHOTTKY RECTIFIER

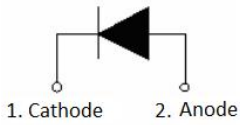


TO-247AC(TO-247-2)

Description

S5D25170H is a SiC Schottky rectifier packaged in TO-247AC(TO-247-2) case. The device is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S5D25170H is ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb − Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	1700	V
Average Rectified Forward Current	$I_{F\ (AV)1}$	Tc=25°C	66	A
	$I_{F\ (AV)2}$	Tc=146°C	25	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM1}	10ms, Half Sine pulse, Tc =25°C	280	A
	I_{FSM2}	10ms, Half Sine pulse, Tc =110°C	210	A
Repetitive Peak Forward Surge Current	I_{FRM1}	10 ms, Half Sine pulse , Tc =25°C	168	A
	I_{FRM2}	10 ms, Half Sine pulse , Tc =110°C	122	A
Power Dissipation	P_{tot1}	Tc =25℃	384.6	W
	P_{tot2}	Tc =110℃	166.7	W

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Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 25A, Pulse, T_J = 25 °C	1.55	1.8	V
	V_{F2}	@ 25A, Pulse, T_J = 175 °C	2.5	3.0	V
Reverse Current*	I_{R1}	@V_R = rated V_R, T_J = 25 °C	1	10	uA
	I_{R2}	@V_R = rated V_R, T_J = 175 °C	20	200	uA
Junction Capacitance	C_{T1}	VR=0V, f=1MHz, Tj=25℃,	2252	-	pF
	C_{T2}	VR=1700V, f=1MHz, Tj=25℃,	98	-	pF
Reverse Recovery Charge	Q_c	I_F = 25A, di/dt = 200A/μs V_R = 1700 V, T_J =25°C	279	-	nC
Capacitance Stored Energy	E_C	V_R = 1700 V, T_J =25°C	303	-	μJ

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation, Tj=25℃	0.39	°C/W

Ordering Information

Device	Package	Shipping
S5D25170H	TO-247AC(TO-247-2)	25pcs / tube

Ratings and Characteristics Curves

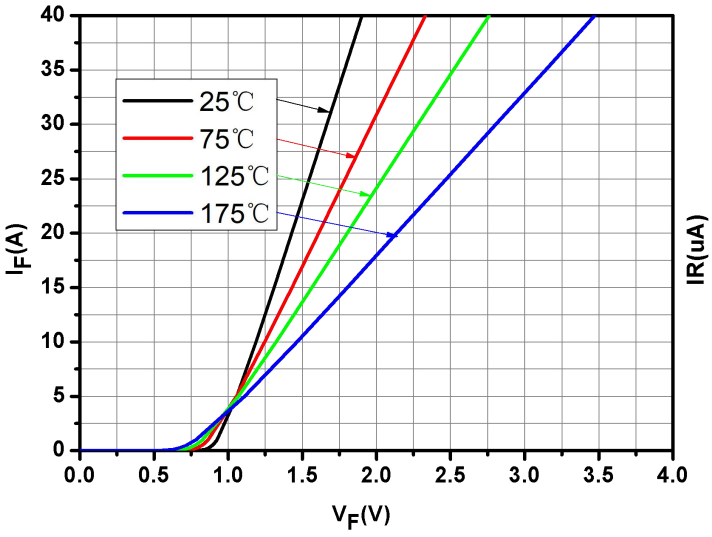

Fig.1-Typical Forward Voltage Characteristics

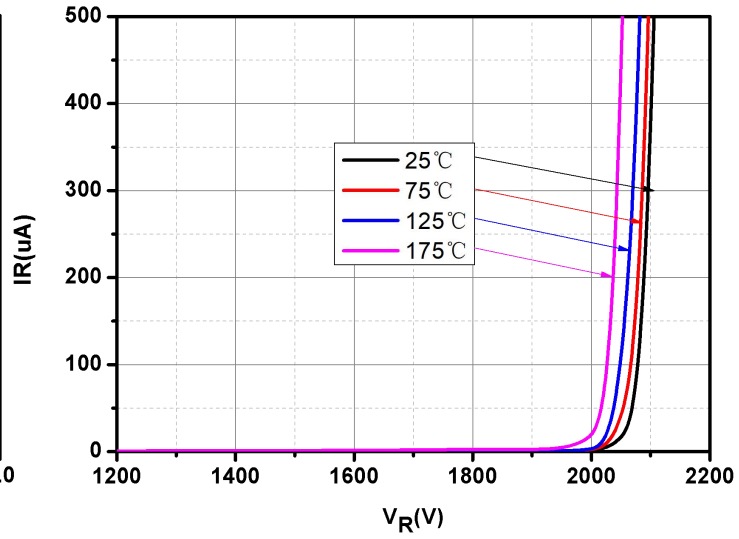

Fig.2-Typical Reverse Characteristics

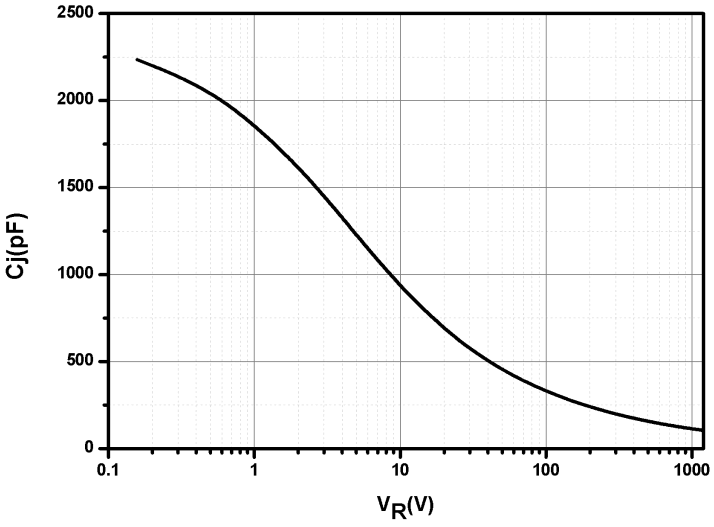

Fig.3-Capacitance vs. Reverse Voltage

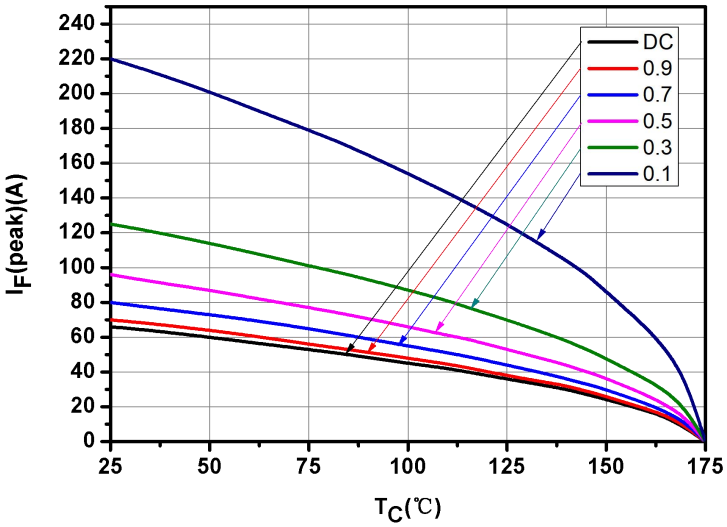

Fig.4-Current Derating

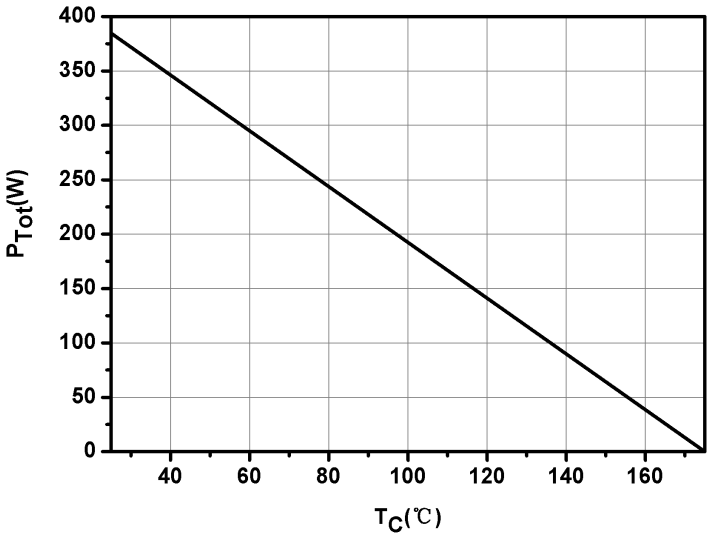

Fig.5-Power Derating

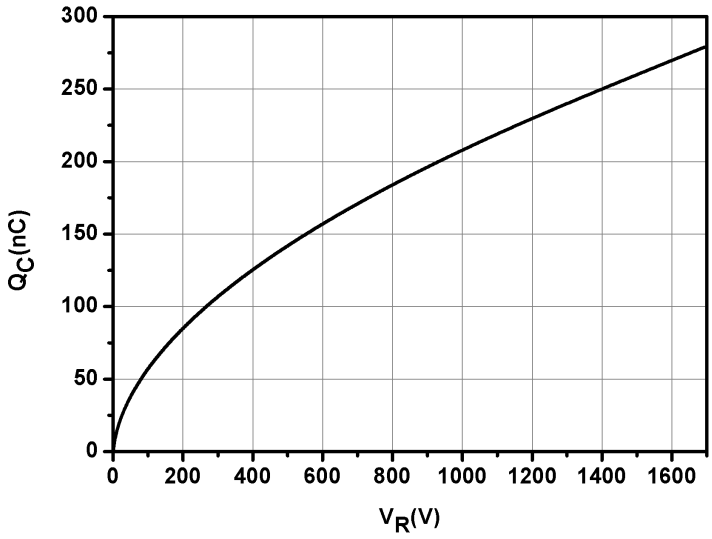

Fig.6-Total Capacitance Charge vs. Reverse Voltage

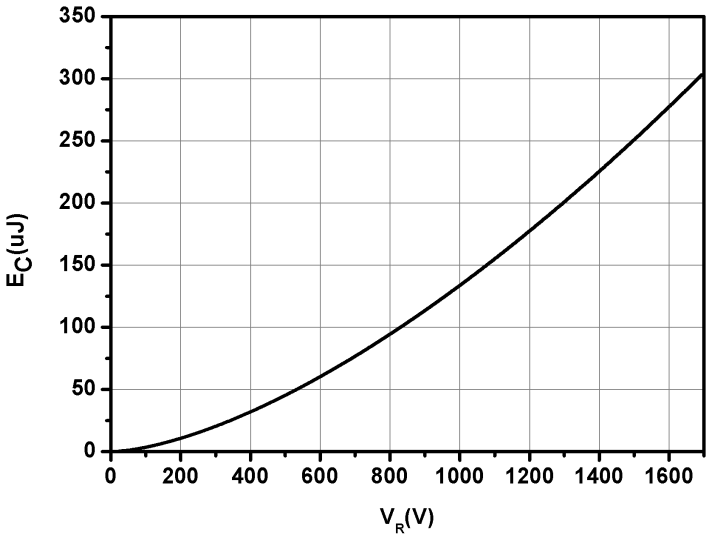

Fig.7-Capacitance Stored Energy

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RoHS

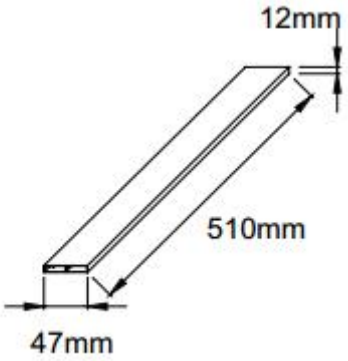
Marking Diagram

Where XXXXX is YYWWL

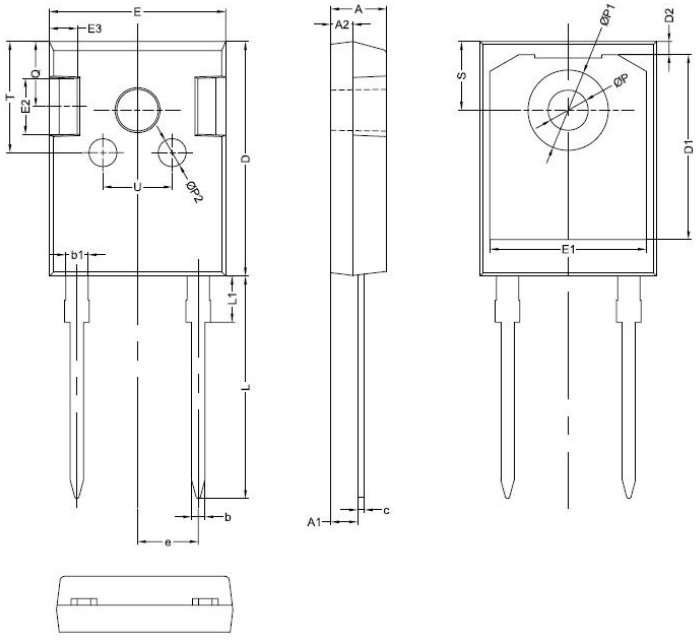
S5D = Device Type
H = Package type
25 = Forward Current (40A)
170 = Reverse Voltage (1200V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Tube Specification(TO-247AC(TO-247-2))



Mechanical Dimensions TO-247AC(TO-247-2)



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

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